220 to 725 MHz Ultra-low Jitter Differential Oscillator



## Features

- AEC-Q100 with extended temperature range (-40°C to 105°C)
- Any frequency between 220.000001 MHz and 725 MHz, accurate to 6 decimal places. For frequency between 1 and 220 MHz, see SiT9386
- LVPECL, LVDS and HCSL output signaling
- Frequency stability as low as ±25 ppm contact SiTime
- 0.23 ps RMS (typ) phase jitter (random, 12 kHz to 20 MHz)
- Industry-standard packages: 3.2 x 2.5, 7.0 x 5.0 mm
- Contact SiTime for 5.0 x 3.2 mm package

## **Electrical Characteristics**

## Applications

- 100 Gbps Ethernet, SONET, SATA, SAS, Fibre Channel
- Telecom, networking, instrumentation, storage, servers



All Min and Max limits in the Electrical Characteristics tables are specified over temperature and rated operating voltage with standard output termination show in the termination diagrams. Typical values are at 25°C and nominal supply voltage.

#### Table 1. Electrical Characteristics – Common to LVPECL, LVDS and HCSL

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
			Freq	uency Range	e	
Output Frequency Range	f	220.000001	-	725	MHz	Accurate to 6 decimal places
			Frequ	ency Stabili	ty	
Frequency Stability		-25	-	+25	ppm	Inclusive of initial tolerance, operating temperature, rated power supply voltage and load variations. Contact SiTime for ± 25 ppm.
		-50	-	+50	ppm	Inclusive of initial tolerance, operating temperature, rated power supply voltage and load variations.
First Year Aging	F_aging1	-	±1	-	ppm	At 25°C
			Temp	erature Rang	ge	
Operating Temperature Range	T use	-40	-	+85	°C	Industrial
Operating reinperature Kange	I_use	-40	-	+105	°C	Extended Industrial
			Sup	oply Voltage		
Supply Voltage	Vdd	2.97	3.30	3.63	V	
		2.70	3.00	3.30	V	
		2.52	2.80	3.08	V	
		2.25	2.50	2.75	V	
			Input C	Characteristi	ics	
Input Voltage High	VIH	70%	-	-	Vdd	Pin 1, OE
Input Voltage Low	VIL	-	-	30%	Vdd	Pin 1, OE
Input Pull-up Impedance	Z_in	-	100	-	kΩ	Pin 1, OE logic high or logic low
			Output	Characteris	tics	
Duty Cycle	DC	45	-	55	%	
			Startup	and OE Tim	ning	
Startup Time	T_start	_	-	3.0	ms	Measured from the time Vdd reaches its rated minimum value.
OE Enable/Disable Time	T_oe	-	3.8		μs	f = 322.265652 MHz

## Table 2. Electrical Characteristics – LVPECL Specific

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
			C	urrent Cor	nsumptio	n
Current Consumption	Idd	-	-	94	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V
OE Disable Supply Current	I_OE	-	-	63	mA	OE = Low
Output Disable Leakage Current	I_leak	-	0.15	-	μA	OE = Low
Maximum Output Current	I_driver	-	-	32	mA	Maximum average current drawn from OUT+ or OUT-
			Οι	utput Char	acteristic	:s
Output High Voltage	VOH	Vdd-1.1	-	Vdd-0.7	V	
Output Low Voltage	VOL	Vdd-1.9	-	Vdd-1.5	V	
Output Differential Voltage Swing	V_Swing	1.2	1.6	2.0	V	See Figure 3
Rise/Fall Time	Tr, Tf	-	225		ps	20% to 80%
				Jitt	er	
RMS Phase Jitter (random)	T_phj		0.225		ps	f=322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, Includes spurs. 7.0 x 5.0 mm package.
		-	0.225		ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, Includes spurs. 3.2 x 2.5 mm package.
		-	0.1		ps	f = 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, Includes spurs, all Vdd levels
RMS Period Jitter <sup>[1]</sup>	T_jitt	-	1.0		ps	f = 322.265625 MHz, Vdd = 3.3V or 2.5V

Notes:

1. Measured according to JESD65B

### Table 3. Electrical Characteristics – LVDS Specific

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
			C	urrent Co	nsumptio	n
Current Consumption	ldd	-	_	89	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V
OE Disable Supply Current	I_OE	-	-	67	mA	OE = Low
Output Disable Leakage Current	I_leak	-	0.15	-	μA	OE = Low
			Οι	Itput Cha	racteristic	25
Differential Output Voltage	VOD	250	-	455	mV	See Figure 4
VOD Magnitude Change	ΔVOD	-	-	50	mV	See Figure 4
Offset Voltage	VOS	1.125	-	1.375	V	See Figure 4
VOS Magnitude Change	ΔVOS	-	-	50	mV	See Figure 4
Rise/Fall Time	Tr, Tf	-	370		ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 4
				Jitt	er	·
RMS Phase Jitter (random)	T_phj	-	0.215		ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, Includes spurs. 7.0 x 5.0 mm package.
		-	0.235		ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, Includes spurs. 3.2 x 2.5 mm package.
		-	0.1	-	ps	f = 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, Includes spurs, all Vdd levels
RMS Period Jitter <sup>[2]</sup>	T_jitt	-	0.92		ps	f = 322.265625 MHz, Vdd = 3.3V or 2.5V

Notes:

2. Measured according to JESD65B

SiTime

### Table 4. Electrical Characteristics – HCSL Specific

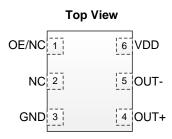
Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
			Curr	rent Consi	umption	
Current Consumption	Idd	-	-	97	mA	Excluding Load Termination Current, Vdd = 3.3V or 2.5V
OE Disable Supply Current	I_OE	-	-	63	mA	OE = Low
Output Disable Leakage Current	I_leak	-	0.15	-	μA	OE = Low
Maximum Output Current	I_driver	-	-	35	mA	Maximum average current drawn from OUT+ or OUT-
			Outp	out Charac	teristics	
Output High Voltage	VOH	0.60	-	0.90	V	See Figure 2
Output Low Voltage	VOL	-0.05	-	0.08	V	See Figure 2
Output Differential Voltage Swing	V_Swing	1.2	1.4	1.9	V	See Figure 3
Rise/Fall Time	Tr, Tf	-	360		ps	Measured with 2 pF capacitive loading to GND, 20% to 80%, see Figure 2
				Jitter		
RMS Phase Jitter (random)	T_phj	I	0.215		ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, Includes spurs. 7.0 x 5.0 mm package.
		-	0.235		ps	f = 322.265625 MHz, Integration bandwidth = 12 kHz to 20 MHz, all Vdd levels, Includes spurs. 3.2 x 2.5 mm package.
		-	0.1		ps	f = 322.265625 MHz, IEEE802.3-2005 10GbE jitter mask integration bandwidth = 1.875 MHz to 20 MHz, Includes spurs, all Vdd levels
RMS Period Jitter <sup>[3]</sup>	T_jitt	-	0.92		ps	f = 322.265625 MHz, Vdd = 3.3V or 2.5V

Notes:

3. Measured according to JESD65

### Table 5. Pin Description

Pin	Мар	Functionality					
	05/00	Output Enable (OE)	H <sup>[4]</sup> : specified frequency output L: output is high impedance				
1	1 OE/NC	Non Connect		H or L or Open: No effect on output frequency or other device functions			
2	NC	NA	No Connect; Leave it floating or connect to GND for better heat dissipation				
3	GND	Power	Vdd Power Supply Ground				
4	OUT+	Output	Oscillator output				
5	OUT-	Output	Complementary oscillator output				
6	Vdd	Power	Power supply voltage <sup>[5]</sup>				



'ime'

### Figure 1. Pin Assignments

Notes:

4. In OE mode, a pull-up resistor of 10 k $\Omega$  or less is recommended if pin 1 is not externally driven.

5. A capacitor of value 0.1  $\mu$ F or higher between Vdd and GND is required. An additional 10  $\mu$ F capacitor between Vdd and GND is required for the best phase jitter performance



#### **Table 6. Absolute Maximum Ratings**

Attempted operation outside the absolute maximum ratings may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

Parameter	Min.	Max.	Unit
Vdd	-0.5	4.0	V
VIH		Vdd + 0.3V	V
VIL	-0.3		V
Storage Temperature	-65	150	°C
Maximum Junction Temperature		130	°C
Soldering Temperature (follow standard Pb-free soldering guidelines)		260	°C

### Table 7. Thermal Considerations<sup>[6]</sup>

Package	$ heta_{ extsf{JA}}$ , 4 Layer Board (°C/W)	$ heta_{ extsf{JC}}$ , Bottom (°C/W)
3225, 6-pin	80	30
7050, 6-pin	52	19

Notes:

6. Refer to JESD51 for  $\theta_{JA}$  and  $\theta_{JC}$  definitions, and reference layout used to determine the  $\theta_{JA}$  and  $\theta_{JC}$  values in the above table.

### Table 8. Maximum Operating Junction Temperature<sup>[7]</sup>

Max Operating Temperature (ambient)	Maximum Operating Junction Temperature
70°C	95°C
85°C	110°C
105°C	_

Notes:

7. Datasheet specifications are not guaranteed if junction temperature exceeds the maximum operating junction temperature.

#### **Table 9. Environmental Compliance**

Parameter	Test Conditions	Value	Unit
Mechanical Shock Resistance	MIL-STD-883F, Method 2002	10,000	g
Mechanical Vibration Resistance	MIL-STD-883F, Method 2007	70	g
Soldering Temperature (follow standard Pb free soldering guidelines)	MIL-STD-883F, Method 2003	260	°C
Moisture Sensitivity Level	MSL1 @ 260°C		
Electrostatic Discharge (HBM)	HBM, JESD22-A114	2,000	V
Charge-Device Model ESD Protection	JESD220C101	750	V
Latch-up Tolerance	JESD78 Con	npliant	



# Waveform Diagrams

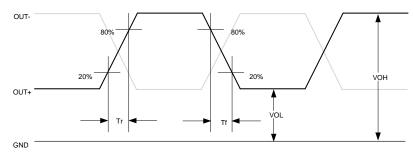


Figure 2. LVPECL/HCSL Voltage Levels per Differential Pin (OUT+/OUT-)

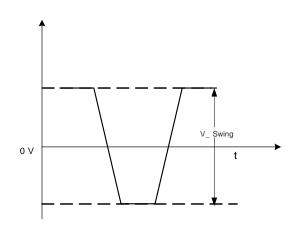
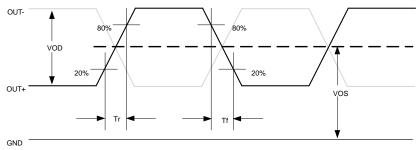
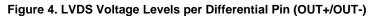


Figure 3. LVPECL/HCSL Voltage Levels across Differential Pair







# **Termination Diagrams**

### LVPECL:

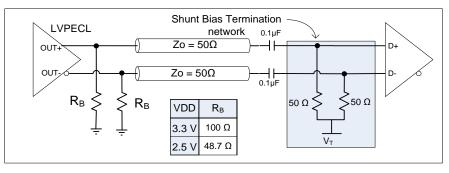


Figure 5. LVPECL with AC-coupled termination

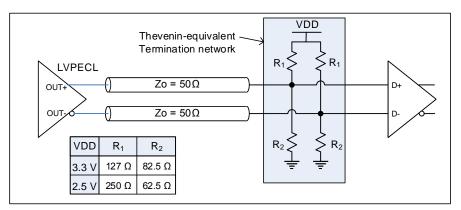


Figure 6. LVPECL DC-coupled load termination with Thevenin equivalent network

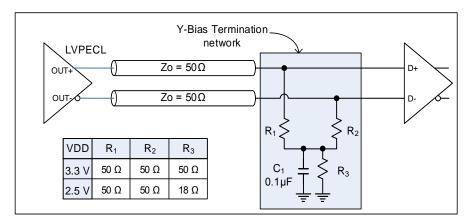


Figure 7. LVPECL with Y-Bias termination



# **Termination Diagrams (Continued)**

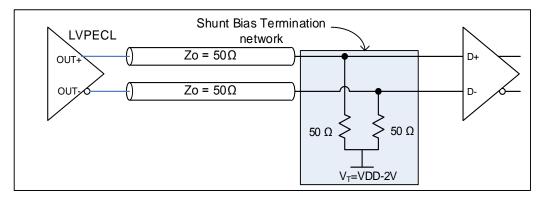


Figure 8. LVPECL with DC-coupled parallel shunt load termination



# **Termination Diagrams (Continued)**

### LVDS:

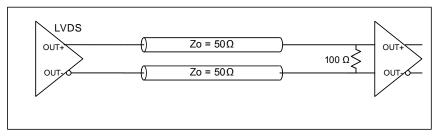


Figure 9. LVDS single DC termination at the load

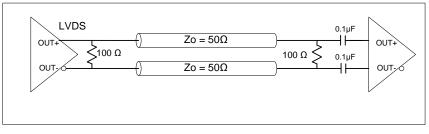


Figure 10. LVDS double AC termination with capacitor close to the load

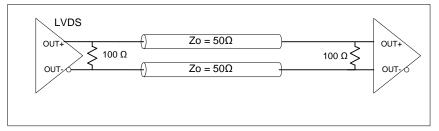


Figure 11. LVDS double DC termination



# **Termination Diagrams (Continued)**

# HCSL:

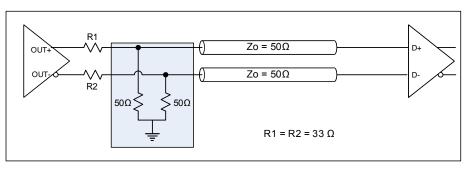
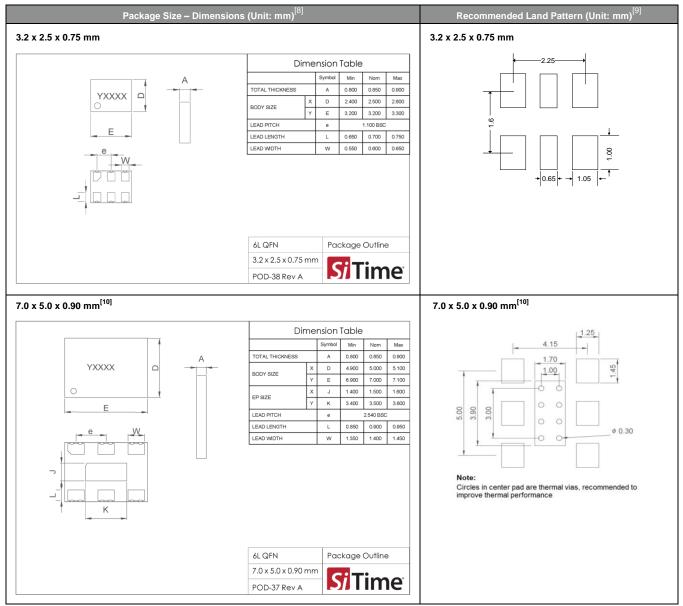


Figure 12. HCSL interface termination



## **Dimensions and Patterns**



Notes:

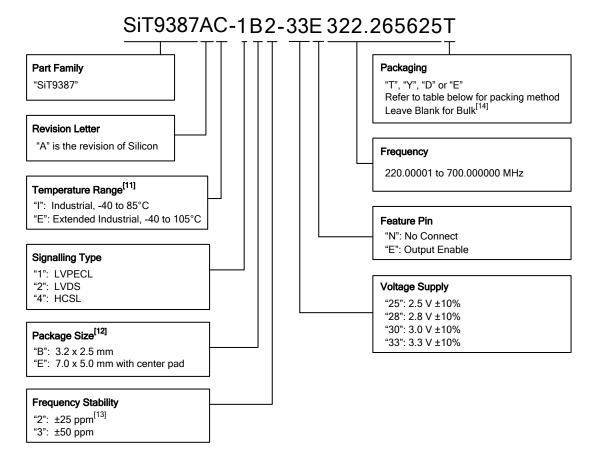
8. Top Marking: Y denotes manufacturing origin and XXXX denotes manufacturing lot number. The value of "Y" will depend on the assembly location of the device.

9. A capacitor of value 0.1 µF or higher between Vdd and GND is required. An additional 10 µF capacitor between Vdd and GND is required for the best phase jitter performance

10. The center pad has no electrical function. Soldering down the center pad to the GND is recommended for best thermal dissipation, but is optional.



## **Ordering Information**



#### Notes:

- 11. Contact SiTime for higher temperature range options
- 12. Contact SiTime for 5.0 x 3.2 mm package
- 13. Contact SiTime for ±25 ppm option
- 14. Bulk is available for sampling only

#### Table 10. Ordering Codes for Supported Tape & Reel Packing Method

Device Size (mm x mm)	8 mm T&R (3ku)	8 mm T&R (1ku)	12 mm T&R (3ku)	12 mm T&R (1ku)	16 mm T&R (3ku)	16 mm T&R (1ku)
7.0 x 5.0	_	_	—	—	Т	Y
3.2 x 2.5	D	E	Т	Y	_	—



#### Table 11 .Revision History

Revision	Release Date	Change Summary
0.90	11/24/2017	Initial release

#### SiTime Corporation, 5451 Patrick Henry Drive, Santa Clara, CA 95054, USA | Phone: +1-408-328-4400 | Fax: +1-408-328-4439

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